

SN74LVC244A Octal Buffer or Driver With 3-State Outputs

1 Features

- Operates from 1.65V to 3.6V
- Inputs accept voltages to 5.5V
- Specified from -40°C to +85°C and -40°C to +125°C
- Maximum t_{pd} of 5.9ns at 3.3V
- Typical V_{OLP} (output ground bounce) < 0.8V at $V_{CC} = 3.3V$, $T_A = 25$ °C
- Typical V_{OHV} (output V_{OH} undershoot) $> 2V \text{ at } V_{CC} = 3.3V, T_A = 25^{\circ}C$
- Supports mixed-mode signal operation on all ports (5V input or output voltage with 3.3V V_{CC})
- I_{off} supports live insertion, partial-power-down mode, and back-drive protection
- Can be used as a down translator to translate inputs from a maximum of 5.5V down to the V_{CC} level
- Available in ultra small logic QFN package (0.5mm maximum height)
- Latch-up performance exceeds 250mA per JESD 17

2 Applications

- Servers
- LED displays
- Network switches
- Telecom infrastructure
- Motor drivers
- I/O expanders

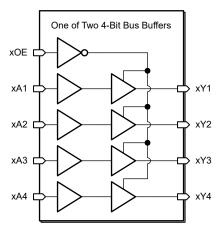
3 Description

These octal bus buffers are designed for 1.65V to 3.6V V_{CC} operation. The SN74LVC244A devices are designed for asynchronous communication between data buses.

Package Information

	. ac.agc		
PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE(2)	BODY SIZE(3)
	RKS (VQFN, 20)(4)	4.50mm × 2.50mm	4.50mm × 2.50mm
	N (PDIP, 20)	24.33mm × 9.4mm	24.33mm × 6.35mm
	NS (SOP, 20)	12.60mm × 7.8mm	12.60mm × 5.30mm
	DB (SSOP, 20)	7.2mm × 7.8mm	7.2mm × 5.30mm
SN74LVC244A	DGV (TVSOP, 20)	5.00mm × 6.4mm	5.00mm × 4.4mm
3N/4LVC244A	DW (SOIC, 20)	12.80mm × 10.3mm	12.80mm × 7.50mm
	RGY (VQFN, 20)	4.50mm × 3.50mm	4.50mm × 3.50mm
	ZQN (BGA, 20)	4.00mm × 3.00mm	4.00mm × 3.00mm
	PW (TSSOP, 20)	6.50mm × 6.4mm	6.50mm × 4.40mm
	RWP (X1QFN, 20)	3.30mm × 2.50mm	3.30mm × 2.50mm

- For more information, see Mechanical, Packaging, and Orderable Information.
- The package size (length × width) is a nominal value and includes pins, where applicable.
- The body size (length × width) is a nominal value and does not include pins.
- (4) **Product Preview**



Logic Diagram (Positive Logic)



Table of Contents

1 Features	1	7.3 Feature Description	11
2 Applications	1	7.4 Device Functional Modes	
3 Description		8 Application and Implementation	13
4 Pin Configuration and Functions	3	8.1 Application Information	13
5 Specifications	5	8.2 Typical Application	13
5.1 Absolute Maximum Ratings	5	8.3 Power Supply Recommendations	14
5.2 ESD Ratings		8.4 Layout	14
5.3 Recommended Operating Conditions	6	9 Device and Documentation Support	16
5.4 Thermal Information	6	9.1 Documentation Support	16
5.5 Electrical Characteristics	7	9.2 Receiving Notification of Documentation Updates	s16
5.6 Switching Characteristics	8	9.3 Support Resources	16
5.7 Operating Characteristics	. 8	9.4 Trademarks	
5.8 Typical Characteristics	9	9.5 Electrostatic Discharge Caution	16
6 Parameter Measurement Information		9.6 Glossary	16
7 Detailed Description	.11	10 Revision History	16
7.1 Overview		11 Mechanical, Packaging, and Orderable	
7.2 Functional Block Diagram	11	Information	17
-			

4 Pin Configuration and Functions

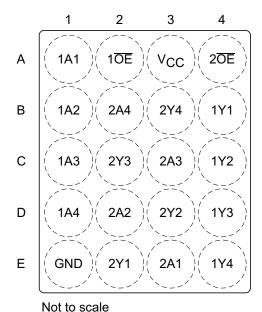


Figure 4-1. ZQN Package 20-Pin BGA Top View

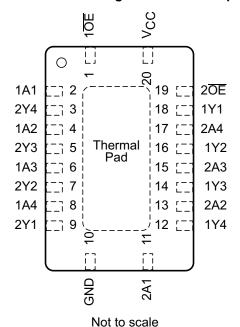


Figure 4-3. RGY and RKS Packages 20-Pin VQFN Top View

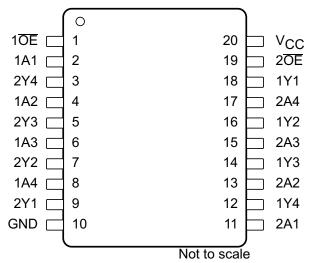


Figure 4-2. DB, DGV,DW, N, NS, and PW Packages 20-Pin SSOP, TVSOP, SOIC, PDIP, SO, and TSSOP Front View

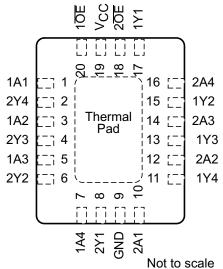


Figure 4-4. RWP Package 20-Pin X1QFN Top View



Table 4-1. Pin Functions

	PIN							
NAME	DB, DGV, DW, N, NS, PW, RGY and RKS	ZQN	RWP	TYPE	DESCRIPTION			
1A1	2	A1	1	I	Port 1 A1 input			
1A2	4	B1	3	I	Port 1 A2 input			
1A3	6	C1	5	I	Port 1 A3 input			
1A4	8	D1	7	I	Port 1 A4 input			
1 ŌE	1	A2	20	I	Output enable			
1Y1	18	B4	17	0	Port 1 Y1 output			
1Y2	16	C4	15	0	Port 1 Y2 output			
1Y3	14	D4	13	0	Port 1 Y3 output			
1Y4	12	E4	11	0	Port 1 Y4 output			
2A1	11	E3	10	I	Port 2 A1 input			
2A2	13	D2	12	I	Port 2 A2 input			
2A3	15	C3	14	I	Port 2 A3 input			
2A4	17	B2	16	I	Port 2 A4 input			
2 OE	19	A4	18	I	Output enable			
2Y1	9	E2	8	0	Port 2 Y1 output			
2Y2	7	D3	6	0	Port 2 Y2 output			
2Y3	5	C2	4	0	Port 2 Y3 output			
2Y4	3	В3	2	0	Port 2 Y4 output			
GND	10	E1	9	_	Ground			
V _{CC}	20	A3	19	_	Power pin			



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	6.5	V
VI	Input voltage ⁽²⁾		-0.5	6.5	V
Vo	Voltage range applied to any output in the high-	impedance or power-off state ⁽²⁾	-0.5	6.5	V
Vo	Voltage range applied to any output in the high	or low state ^{(2) (3)}	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
P _{tot}	Power dissipation	$T_A = -40^{\circ}\text{C to } +125^{\circ}\text{C}^{(4)}$ (5)		500	mW
TJ	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Section 5.3 is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The value of V_{CC} is provided in the Section 5.3 table.
- (4) For the DW package: above 70°C the value of P_{tot} derates linearly with 8 mW/K.
- (5) For the DB, DGV, N, NS, and PW packages: above 60°C the value of Ptot derates linearly with 5.5 mW/K.

5.2 ESD Ratings

			VALUE	UNIT
V	\/	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
V _(ESD) Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

Copyright © 2025 Texas Instruments Incorporated

Submit Document Feedback



5.3 Recommended Operating Conditions

over recommended operating free-air temperature range (unless otherwise noted)(1)

			T _A = 25°C -40 TO +85°C		+85°C	-40 TO	+125°C	UNIT		
			MIN	MAX	MIN	MAX	MIN	MAX	UNII	
.,	Cumply valtage	Operating	1.65	3.6	1.65	3.6	1.65	3.6	V	
V _{CC}	Supply voltage	Data retention only	1.5		1.5		1.5		V	
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		0.65 × V _{CC}		0.65 × V _{CC}			
V _{IH}	High-level input voltage	V _{CC} = 2.3 V to 2.7 V	1.7		1.7		1.7		V	
		V _{CC} = 2.7 V to 3.6 V	2		2		2			
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}		0.35 × V _{CC}		0.35 × V _{CC}		
V _{IL}	Low-level input voltage	V _{CC} = 2.3 V to 2.7 V		0.7		0.7		0.7	V	
		V _{CC} = 2.7 V to 3.6 V		0.8		0.8		0.8		
Vı	Input voltage		0	5.5	0	5.5	0	5.5	V	
Vo	Output voltage		0	V _{CC}	0	V _{CC}	0	V _{CC}	V	
		V _{CC} = 1.65 V		-4		-4		-4		
١.	High-level	V _{CC} = 2.3 V		-8		-8		-8	^	
I _{OH}	output current	V _{CC} = 2.7 V		-12		-12		-12	mA	
		V _{CC} = 3 V		-24		-24		-24		
		V _{CC} = 1.65 V		4		4		4		
١.	Low-level	V _{CC} = 2.3 V		8		8		8	т Л	
I _{OL}	output current	V _{CC} = 2.7 V		12		12		12	mA	
		V _{CC} = 3 V		24		24		24		
_	Ambient	BGA package			-40	85			°C	
T _A	temperature	All other packages					-40	125	C	

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.

5.4 Thermal Information

					S	N74LVC2	244A					
	THERMAL METRIC ⁽¹⁾		DGV ⁽²⁾ (TVSOP)	DW ⁽²⁾ (SOIC)	ZQN ⁽²⁾ (BGA)	N ⁽²⁾ (PDIP)	NS ⁽²⁾ (SO)	PW ⁽²⁾ (TSSOP	RGY ⁽³⁾ (VQFN)	RWP ⁽³⁾ (X1QFN)	RKS ⁽³⁾ (VQFN)	UNIT
						20 PIN	S					
$R_{\theta JA}$	Junction-to-ambient thermal resistance	108.1	128.7	90.9	198.7	61.6	90.1	114.7	50.3	79.9	87.2	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	70.2	43.7	55.3	106.8	46.5	56.4	48.4	58.4	63.2	93.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	63.3	70.2	58.8	143.1	42.5	57.7	65.6	28.3	46.4	59.8	°C/W
Ψлт	Junction-to-top characterization parameter	30.6	3.1	29.1	24.1	34.6	28.4	6.8	4.9	2.6	24.9	°C/W
ΨЈВ	Junction-to-board characterization parameter	62.9	69.5	58.3	119.6	42.4	57.2	65.1	28.4	46.3	59.6	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	_	_	_	n/a	_	_	_	22.7	27.3	44.3	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report

Product Folder Links: SN74LVC244A

⁽²⁾ The package thermal impedance is calculated in accordance with JESD 51-7.

⁽³⁾ The package thermal impedance is calculated in accordance with JESD 51-5.



5.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V	T _A =	25°C		-40 TO +8	5°C	-40 TO +12	25°C	UNIT	
PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNII	
	I _{OH} = -100 μA	1.65 V to 3.6 V	V _{CC} - 0.2			V _{CC} - 0.2		V _{CC} - 0.3			
	I _{OH} = -4 mA	1.65 V	1.29			1.2		1.05			
V _{OH}	I _{OH} = -8 mA	2.3 V	1.9			1.7		1.55		V	
	I _{OH} = -12 mA	2.7 V	2.2			2.2		2.05			
	10H 12 MA	3 V	2.4			2.4		2.25			
	I _{OH} = -24 mA	3 V	2.3			2.2		2			
	I _{OL} = 100 μA	1.65 V to 3.6 V			0.1		0.2		0.3		
V_{OL}	I _{OL} = 4 mA	1.65 V			0.24		0.45		0.6	V	
· OL	I _{OL} = 8 mA	2.3 V			0.3		0.7		0.75	·	
	I _{OL} = 12 mA	2.7 V			0.4		0.4		0.6		
	I _{OL} = 24 mA	3 V			0.55		0.55		0.8		
I _I	V _I = 5.5 V or GND	3.6 V			±1		±5		±20	μΑ	
I _{off}	V _I or V _O = 5.5 V	0			±1		±10		±20	μΑ	
I_{OZ}	V _O = 0 to 5.5 V	3.6 V			±1		±10		±20	μΑ	
la a	$V_I = V_{CC}$ or GND $I_O = 0$	3.6 V			1		10		40	μA	
I _{CC}	$3.6 \text{ V} \le \text{V}_1 \le 5.5 \text{ V}^{(1)}$	3.0 V			1		10		40	μΛ	
ΔI _{CC}	One input at $V_{CC} - 0.6 \text{ V}$, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500		500		5000	μΑ	
C _i	V _I = V _{CC} or GND	3.3 V		4						pF	
C _o	V _O = V _{CC} or GND	3.3 V		5.5						pF	

⁽¹⁾ This applies in the disabled state only.



5.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6-1)

DADAMETED	FROM	то	· ·	TA	_λ = 25°C		-40 TO +85	C	-40 TO +125°C	LINUT
PARAMETER	(INPUT)	(OUTPUT)	V _{cc}	MIN	TYP	MAX	MIN N	IAX	MIN MAX	UNIT
			1.5 V		7	14.4		4.9	16.4	
			1.8 V ± 0.15 V		5.9	10.4		0.9	12.4	
t _{pd}	Α	Y	2.5 V ± 0.2 V		4.2	7.4		7.9	10	ns
			2.7 V		4.2	6.7		6.9	8.2	
			3.3 V ± 0.3 V		3.9	5.7		5.9	7.2	
	ŌĒ	Y	1.5 V		8.3	17.8		8.3	19.8	
			1.8 V ± 0.15 V		6.4	12.1		2.6	14.1	ns
t _{en}			2.5 V ± 0.2 V		4.6	9.1		9.6	11.7	
			2.7 V		5	8.4		8.6	10.3	
			3.3 V ± 0.3 V		4.5	7.4		7.6	9.4	
			1.5 V		7.2	15.6		6.1	17.6	
			1.8 V ± 0.15 V		5.8	11.6		2.1	13.6	
t _{dis}	ŌĒ	Y	2.5 V ± 0.2 V		3.7	7.3		7.8	9.9	ns
			2.7 V		3.8	6.6		6.8	8.6	
			3.3 V ± 0.3 V		3.8	6.3		6.5	8	
t _{sk(o)}			3.3 V ± 0.3 V					1	1.5	ns

5.7 Operating Characteristics

 $T_{\Lambda} = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	V _{CC}	TYP	UNIT	
			1.8 V	43		
	Outputs enabled	f = 10 MHz	2.5 V	43		
	Dower discinction conscitance per buffer/driver			3.3 V	44	pF
C _{pd}	Power dissipation capacitance per buffer/driver	Outputs disabled		1.8 V	1	pr
			f = 10 MHz	2.5 V	1	
				3.3 V	2	

Product Folder Links: SN74LVC244A

5.8 Typical Characteristics

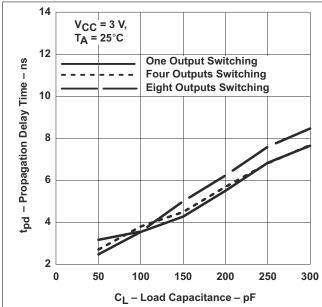


Figure 5-1. Propagation Delay (Low to High Transition)
vs Load Capacitance

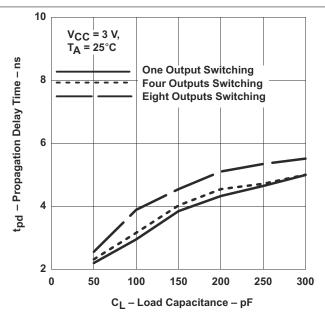
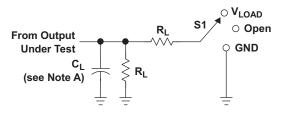


Figure 5-2. Propagation Delay (High to Low Transition)
vs Load Capacitance



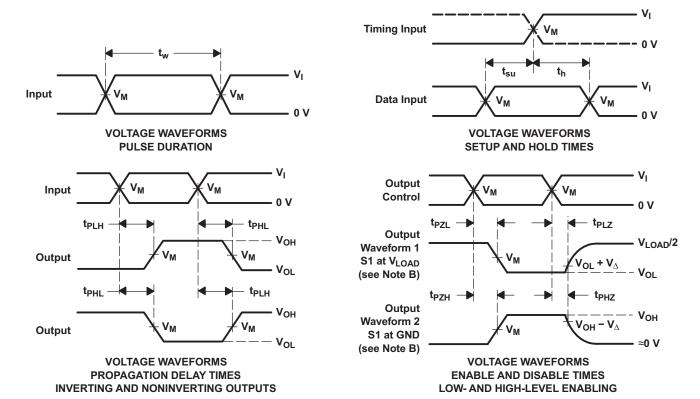
6 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V_{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

V	INPUTS		V	V		Б	V
V _{CC}	VI	t _r /t _f	V _M	V _{LOAD}	CL	R_L	$V_{\!\scriptscriptstyle \Delta}$
1.5 V	V _{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	15 pF	2 k Ω	0.1 V
1.8 V ± 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	30 pF	1 k Ω	0.15 V
2.5 V ± 0.2 V	V _{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	30 pF	500 Ω	0.15 V
2.7 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
3.3 V ± 0.3 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V



NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 6-1. Load Circuit and Voltage Waveforms

Submit Document Feedback

Copyright © 2025 Texas Instruments Incorporated

7 Detailed Description

7.1 Overview

The SN74LVC244A contains 8 individual high speed CMOS buffers organized as two 4-bit buffers/line drives with 3-state outputs.

Each buffer performs the boolean logic function xYn = xAn, with x being the bank number and n being the channel number.

Each output enable $(x\overline{OE})$ controls four buffers. When the $x\overline{OE}$ pin is in the low state, the outputs of all buffers in the bank x are enabled. When the $x\overline{OE}$ pin is in the high state, the outputs of all buffers in the bank x are disabled. All disabled output are placed into the high-impedance state.

To put the device in the high-impedance state during power up or power down, tie both \overline{OE} pins to V_{CC} through a pull-up resistor; the minimum value of the resistor is determined by the current sinking capability of the driver and the leakage of the pin as defined in the *Electrical Characteristics* table.

7.2 Functional Block Diagram

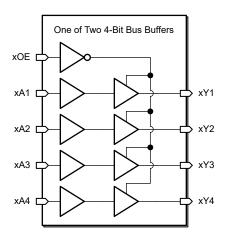


Figure 7-1. Logic Diagram (Positive Logic)

7.3 Feature Description

7.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-state outputs. Driving high, driving low, and high impedance are the three states that these outputs can be in. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device can drive larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance state, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a $10k\Omega$ resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

7.3.2 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law (R = V ÷ I).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in *Implications of Slow or Floating CMOS Inputs*.

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a $10k\Omega$ resistor, however, is recommended and will typically meet all requirements.

7.3.3 Clamp Diode Structure

Figure 7-2 shows the inputs and outputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

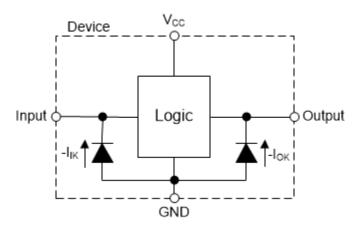


Figure 7-2. Electrical Placement of Clamping Diodes for Each Input and Output

7.4 Device Functional Modes

Table 7-1 lists the functional modes of the SN74LVC244A.

Table 7-1. Function Table

 H = High Voltage Level, L = Low Voltage Level, X = Do Not Care, Z = High-Impedance State

Submit Document Feedback

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

SN74LVC244A is a high drive CMOS device that can be used for a multitude of bus interface type applications where output drive or PCB trace length is a concern. The inputs can accept voltages to 5.5V at any valid V_{CC} making it ideal for down translation.

8.2 Typical Application

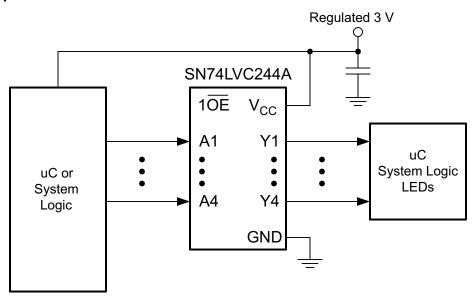


Figure 8-1. Application Schematic

8.2.1 Design Requirements

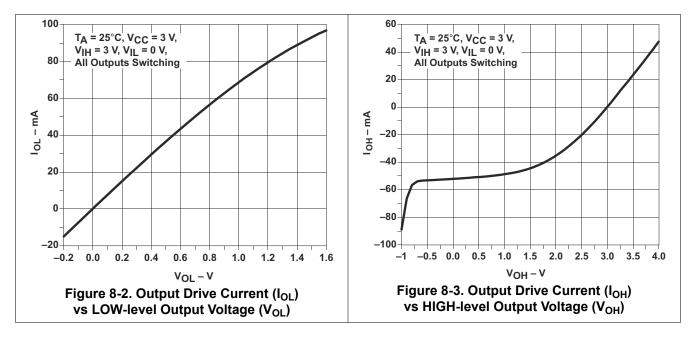
This device uses CMOS technology and has balanced output drive. Avoid bus contention because it can drive currents in excess of maximum limits. The high drive will also create fast edges into light loads, so consider routing and load conditions to prevent ringing.

8.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
 - For rise time and fall time specification, see ($\Delta t/\Delta V$) in the Section 5.3 table.
 - For specified high and low levels, see (V_{IH} and V_{IL}) in the Section 5.3 table.
 - Inputs are overvoltage tolerant allowing them to go as high as (V_I max) in the Section 5.3 table at any valid V_{CC}.
- 2. Recommended maximum Output Conditions:
 - Load currents should not exceed (I_O max) per output and should not exceed (Continuous current through V_{CC} or GND) total current for the part. These limits are located in the Section 5.1 table.
 - Outputs should not be pulled above V_{CC}.



8.2.3 Application Curves



8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A $0.1\mu F$ capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The $0.1\mu F$ and $1\mu F$ capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

8.4 Layout

8.4.1 Layout Guidelines

- Bypass capacitor placement
 - Place near the positive supply terminal of the device
 - Provide an electrically short ground return path
 - Use wide traces to minimize impedance
 - Keep the device, capacitors, and traces on the same side of the board whenever possible
- Signal trace geometry
 - 8mil to 12mil trace width
 - Lengths less than 12cm to minimize transmission line effects
 - Avoid 90° corners for signal traces
 - Use an unbroken ground plane below signal traces
 - Flood fill areas around signal traces with ground
 - For traces longer than 12cm
 - Use impedance controlled traces
 - Source-terminate using a series damping resistor near the output
 - · Avoid branches; buffer signals that must branch separately



8.4.2 Layout Example

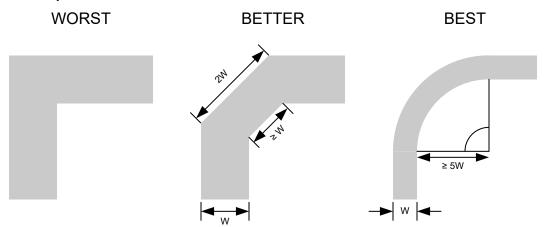


Figure 8-4. Example Trace Corners for Improved Signal Integrity

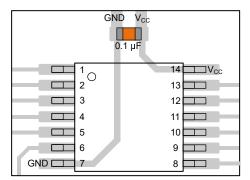


Figure 8-5. Example Bypass Capacitor Placement for TSSOP and Similar Packages

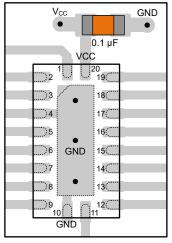


Figure 8-6. Example Bypass Capacitor Placement for WQFN and Similar Packages

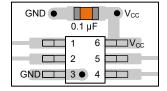


Figure 8-7. Example Bypass Capacitor Placement for SOT, SC70 and Similar Packages



Figure 8-8. Example Damping Resistor Placement for Improved Signal Integrity



9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, CMOS Power Consumption and Cpd Calculation application report
- Texas Instruments, *Designing With Logic* application report
- Texas Instruments, Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices application report

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

(Changes from Revision AC (October 2020) to Revision AD (March 2025)	Page
•	Added RKS (VQFN, 20) package option	1

Changes from Revision AB (November 2016) to Revision AC (October 2020)

Page

Product Folder Links: SN74LVC244A

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

Copyright © 2025 Texas Instruments Incorporated

Submit Document Feedback

www.ti.com

17-Jun-2025

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
PSN74LVC244ARKSR	Active	Preproduction	VQFN (RKS) 20	3000 LARGE T&R	_	Call TI	Call TI	-40 to 125	
PSN74LVC244ARKSR.A	Active	Preproduction	VQFN (RKS) 20	3000 LARGE T&R	-	Call TI	Call TI	-40 to 125	
SN74LVC244ADBR	Active	Production	SSOP (DB) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ADBR.A	Active	Production	SSOP (DB) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ADBR.B	Active	Production	SSOP (DB) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ADBRE4	Active	Production	SSOP (DB) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ADBRG4	Active	Production	SSOP (DB) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ADGVR	Active	Production	TVSOP (DGV) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ADGVR.B	Active	Production	TVSOP (DGV) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ADGVRG4	Active	Production	TVSOP (DGV) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ADGVRG4.B	Active	Production	TVSOP (DGV) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ADW	Active	Production	SOIC (DW) 20	25 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ADW.B	Active	Production	SOIC (DW) 20	25 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ADWE4	Active	Production	SOIC (DW) 20	25 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ADWG4	Active	Production	SOIC (DW) 20	25 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ADWR	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ADWR.A	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ADWR.B	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ADWRG4	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ADWRG4.A	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ADWRG4.B	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244AN	Active	Production	PDIP (N) 20	20 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	SN74LVC244AN
SN74LVC244AN.B	Active	Production	PDIP (N) 20	20 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	SN74LVC244AN
SN74LVC244ANSR	Active	Production	SOP (NS) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ANSR.A	Active	Production	SOP (NS) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ANSR.B	Active	Production	SOP (NS) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ANSRG4	Active	Production	SOP (NS) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ANSRG4.A	Active	Production	SOP (NS) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A
SN74LVC244ANSRG4.B	Active	Production	SOP (NS) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A





17-Jun-2025 www.ti.com

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
SN74LVC244APW	Active	Production	TSSOP (PW) 20	70 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APW.B	Active	Production	TSSOP (PW) 20	70 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWE4	Active	Production	TSSOP (PW) 20	70 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWG4	Active	Production	TSSOP (PW) 20	70 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWR	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWR.A	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWR.B	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWRE4	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWRG3	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWRG3.A	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWRG3.B	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWRG4	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWRG4.A	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWRG4.B	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWT	Active	Production	TSSOP (PW) 20	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWT.B	Active	Production	TSSOP (PW) 20	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWTE4	Active	Production	TSSOP (PW) 20	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244APWTG4	Active	Production	TSSOP (PW) 20	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ARGYR	Active	Production	VQFN (RGY) 20	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LC244A
SN74LVC244ARGYR.A	Active	Production	VQFN (RGY) 20	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LC244A
SN74LVC244ARGYR.B	Active	Production	VQFN (RGY) 20	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LC244A
SN74LVC244ARGYRG4	Active	Production	VQFN (RGY) 20	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LC244A
SN74LVC244ARWPR	Active	Production	X1QFN (RWP) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ARWPR.A	Active	Production	X1QFN (RWP) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ARWPR.B	Active	Production	X1QFN (RWP) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ARWPRG4.A	Active	Production	X1QFN (RWP) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A
SN74LVC244ARWPRG4.B	Active	Production	X1QFN (RWP) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A

⁽¹⁾ Status: For more details on status, see our product life cycle.

PACKAGE OPTION ADDENDUM

www.ti.com 17-Jun-2025

(2) Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

- (3) RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.
- (4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.
- (5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
- (6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC244A:

Automotive: SN74LVC244A-Q1

NOTE: Qualified Version Definitions:

Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



www.ti.com 2-Jul-2025

TAPE AND REEL INFORMATION



TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC244ADBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN74LVC244ADGVR	TVSOP	DGV	20	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LVC244ADGVRG4	TVSOP	DGV	20	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LVC244ADWR	SOIC	DW	20	2000	330.0	24.4	10.9	13.3	2.7	12.0	24.0	Q1
SN74LVC244ADWRG4	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN74LVC244ANSR	SOP	NS	20	2000	330.0	24.4	8.4	13.0	2.5	12.0	24.0	Q1
SN74LVC244ANSRG4	SOP	NS	20	2000	330.0	24.4	8.4	13.0	2.5	12.0	24.0	Q1
SN74LVC244APWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LVC244APWRG3	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
SN74LVC244APWRG4	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LVC244APWT	TSSOP	PW	20	250	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LVC244ARGYR	VQFN	RGY	20	3000	330.0	12.4	3.8	4.8	1.6	8.0	12.0	Q1
SN74LVC244ARWPR	X1QFN	RWP	20	2000	178.0	13.5	2.85	3.65	0.75	8.0	12.0	Q1



www.ti.com 2-Jul-2025



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC244ADBR	SSOP	DB	20	2000	356.0	356.0	35.0
SN74LVC244ADGVR	TVSOP	DGV	20	2000	356.0	356.0	35.0
SN74LVC244ADGVRG4	TVSOP	DGV	20	2000	356.0	356.0	35.0
SN74LVC244ADWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN74LVC244ADWRG4	SOIC	DW	20	2000	367.0	367.0	45.0
SN74LVC244ANSR	SOP	NS	20	2000	367.0	367.0	45.0
SN74LVC244ANSRG4	SOP	NS	20	2000	367.0	367.0	45.0
SN74LVC244APWR	TSSOP	PW	20	2000	356.0	356.0	35.0
SN74LVC244APWRG3	TSSOP	PW	20	2000	364.0	364.0	27.0
SN74LVC244APWRG4	TSSOP	PW	20	2000	356.0	356.0	35.0
SN74LVC244APWT	TSSOP	PW	20	250	356.0	356.0	35.0
SN74LVC244ARGYR	VQFN	RGY	20	3000	356.0	356.0	35.0
SN74LVC244ARWPR	X1QFN	RWP	20	2000	189.0	185.0	36.0

PACKAGE MATERIALS INFORMATION

www.ti.com 2-Jul-2025

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74LVC244ADW	DW	SOIC	20	25	507	12.83	5080	6.6
SN74LVC244ADW.B	DW	SOIC	20	25	507	12.83	5080	6.6
SN74LVC244ADWE4	DW	SOIC	20	25	507	12.83	5080	6.6
SN74LVC244ADWG4	DW	SOIC	20	25	507	12.83	5080	6.6
SN74LVC244AN	N	PDIP	20	20	506	13.97	11230	4.32
SN74LVC244AN.B	N	PDIP	20	20	506	13.97	11230	4.32
SN74LVC244APW	PW	TSSOP	20	70	530	10.2	3600	3.5
SN74LVC244APW.B	PW	TSSOP	20	70	530	10.2	3600	3.5
SN74LVC244APWE4	PW	TSSOP	20	70	530	10.2	3600	3.5
SN74LVC244APWG4	PW	TSSOP	20	70	530	10.2	3600	3.5





NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

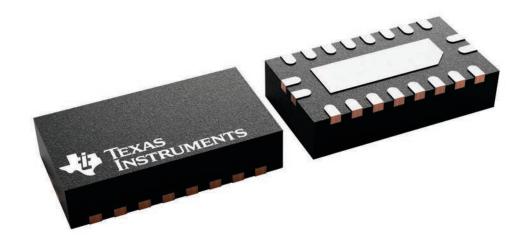
- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



2.5 x 4.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



INSTRUMENTS www.ti.com

MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



3.5 x 4.5, 0.5 mm pitch

PLASTIC QUAD FGLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.





NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



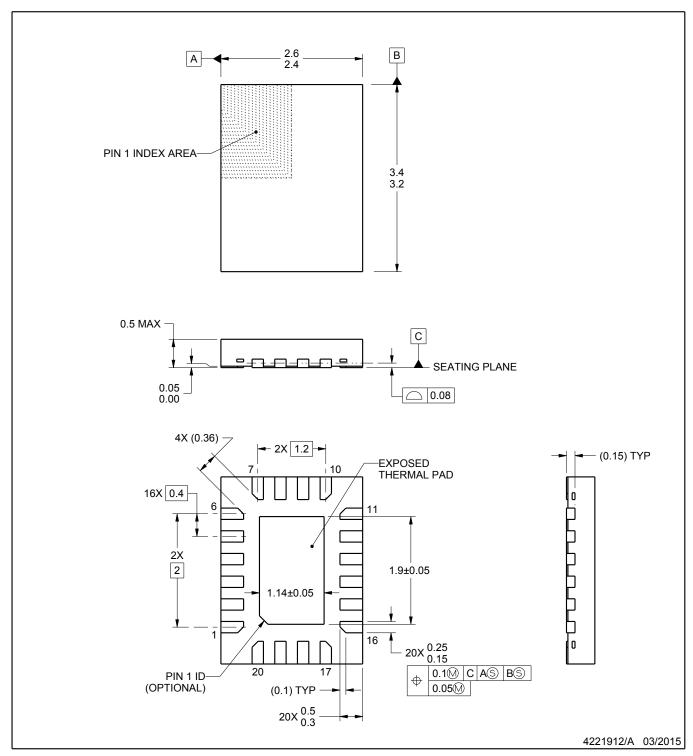


NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



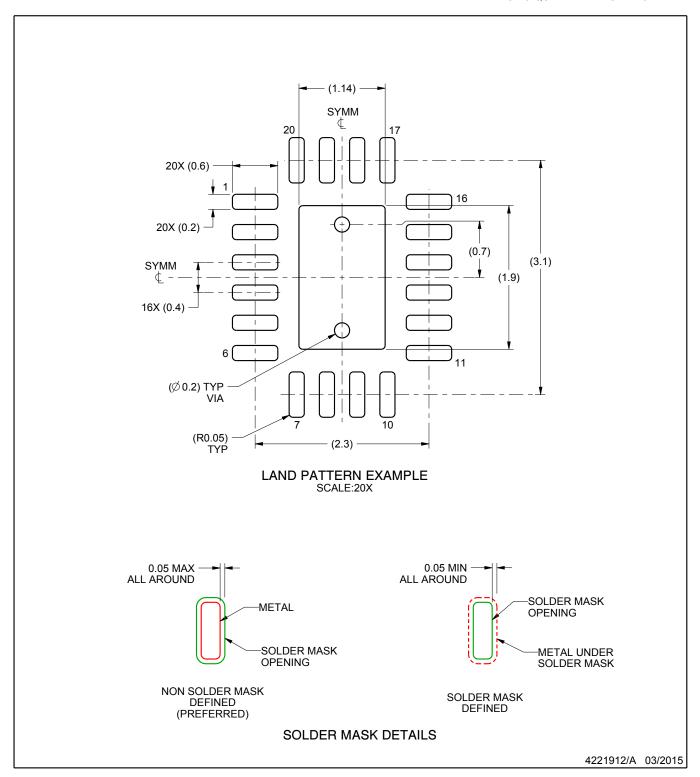




NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

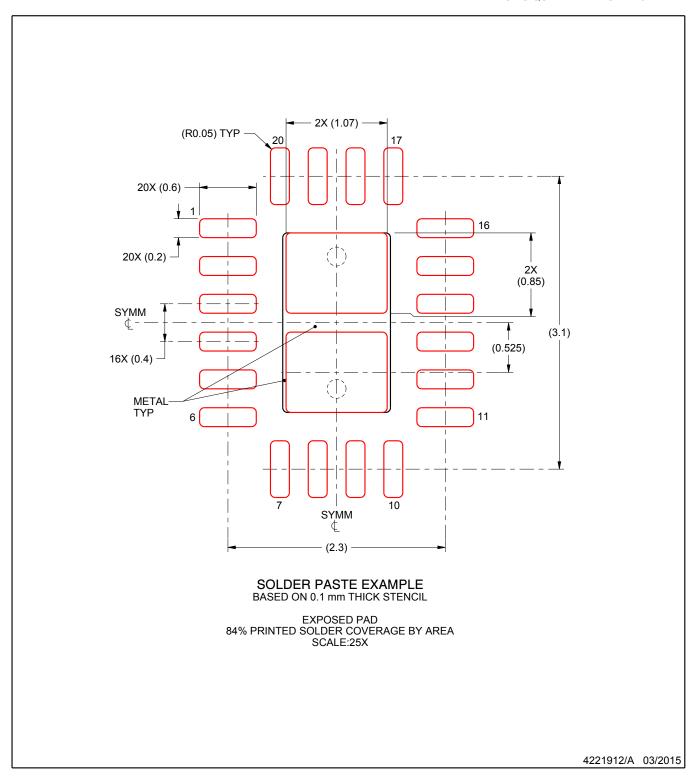




NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).





NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.





SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2025. Texas Instruments Incorporated